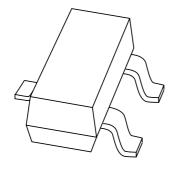
DISCRETE SEMICONDUCTORS

DATA SHEET



PMBT5551 NPN high-voltage transistor

Product data sheet Supersedes data of 1999 Apr 15 2004 Jan 21



NPN high-voltage transistor

PMBT5551

FEATURES

• Low current (max. 300 mA)

• High voltage (max. 160 V).

APPLICATIONS

- General purpose
- Telephony.

DESCRIPTION

NPN high-voltage transistor in a SOT23 plastic package. PNP complement: PMBT5401.

MARKING

| TYPE NUMBER | MARKING CODE ⁽¹⁾ |
|-------------|-----------------------------|
| PMBT5551 | *G1 |

Note

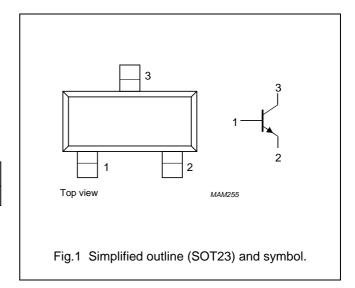
1. * = p: Made in Hong Kong.

* = t : Made in Malaysia. * = W : Made in China.

ORDERING INFORMATION

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | base |
| 2 | emitter |
| 3 | collector |



| TYPE | PACKAGE | | | | | |
|----------|---------|--|-------|--|--|--|
| NUMBER | NAME | NAME DESCRIPTION VERSION | | | | |
| PMBT5551 | _ | plastic surface mounted package; 3 leads | SOT23 | | | |

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------|--------------------------|------|------|------|
| V _{CBO} | collector-base voltage | open emitter | _ | 180 | V |
| V _{CEO} | collector-emitter voltage | open base | _ | 160 | V |
| V_{EBO} | emitter-base voltage | open collector | _ | 6 | V |
| I _C | collector current (DC) | | _ | 300 | mA |
| I _{CM} | peak collector current | | _ | 600 | mA |
| I _{BM} | peak base current | | _ | 100 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | _ | 250 | mW |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | _ | 150 | °C |
| T _{amb} | operating ambient temperature | | -65 | +150 | °C |

NPN high-voltage transistor

PMBT5551

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|----------------------|---|------------|-------|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | note 1 | 500 | K/W |

Note

1. Transistor mounted on an FR4 printed-circuit board.

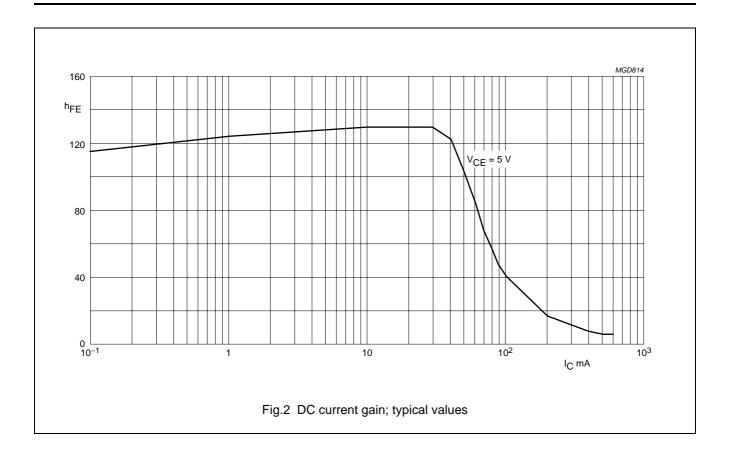
CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|--------------------|--------------------------------------|--|------|------|------|
| I _{CBO} | collector-base cut-off current | I _E = 0; V _{CB} = 120 V | _ | 50 | nA |
| | | I _E = 0; V _{CB} = 120 V; T _{amb} = 100 °C | _ | 50 | μΑ |
| I _{EBO} | emitter-base cut-off current | I _C = 0; V _{EB} = 4 V | _ | 50 | nA |
| h _{FE} | DC current gain | V _{CE} = 5 V; (see Fig.2) | | | |
| | | $I_C = 1 \text{ mA}$ | 80 | _ | |
| | | $I_C = 10 \text{ mA}$ | 80 | 250 | |
| | | $I_C = 50 \text{ mA}$ | 30 | _ | |
| V _{CEsat} | collector-emitter saturation voltage | I _C = 10 mA; I _B = 1 mA | _ | 150 | mV |
| | | I _C = 50 mA; I _B = 5 mA | _ | 200 | mV |
| V _{BEsat} | base-emitter saturation voltage | $I_C = 10 \text{ mA}; I_B = 1 \text{ mA}$ | _ | 1 | V |
| | | $I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$ | _ | 1 | V |
| C _c | collector capacitance | I _E = i _e = 0; V _{CB} = 10 V; f = 1 MHz | _ | 6 | pF |
| C _e | emitter capacitance | $I_C = i_c = 0$; $V_{EB} = 500 \text{ mV}$; $f = 1 \text{ MHz}$ | _ | 30 | pF |
| f _T | transition frequency | I _C = 10 mA; V _{CE} = 10 V; f = 100 MHz | 100 | 300 | MHz |
| F | noise figure | I_C = 200 μA; V_{CE} = 5 V; R_S = 2 kΩ; f = 10 Hz to 15.7 kHz | _ | 8 | dB |

NPN high-voltage transistor

PMBT5551



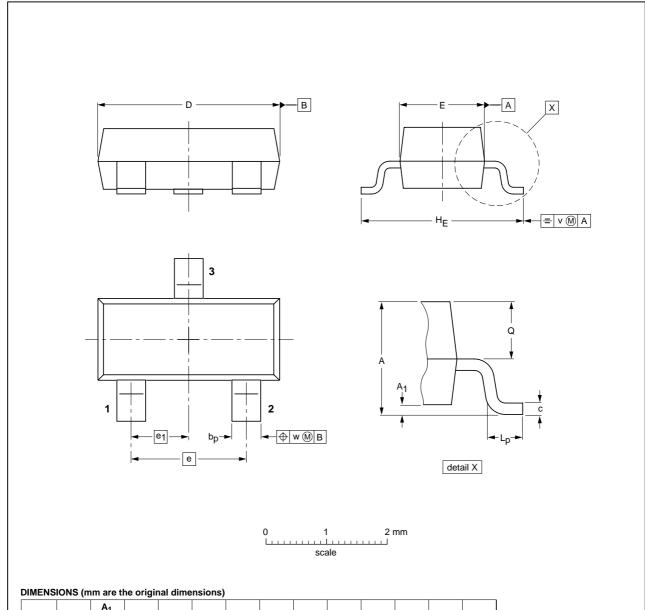
NPN high-voltage transistor

PMBT5551

PACKAGE OUTLINE



SOT23



| ι | JNIT | Α | A ₁ max. | bp | С | D | E | е | e ₁ | HE | Lp | Q | v | w |
|---|------|------------|------------------------|--------------|--------------|------------|------------|-----|----------------|------------|--------------|--------------|-----|-----|
| | mm | 1.1 0.9 | 0.1 | 0.48 0.38 | 0.15 0.09 | 3.0 2.8 | 1.4 1.2 | 1.9 | 0.95 | 2.5 2.1 | 0.45 0.15 | 0.55 0.45 | 0.2 | 0.1 |

| OUTLINE | | REFER | EUROPEAN | ISSUE DATE | | |
|---------|-----|----------|----------|------------|------------|----------------------------------|
| VERSION | IEC | JEDEC | JEITA | | PROJECTION | ISSUE DATE |
| SOT23 | | TO-236AB | | | | -04-11-04 06-03-16 |

NPN high-voltage transistor

PMBT5551

DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|-----------------------------------|----------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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